

- 32. The electrical contact of Claim 24 wherein said silicon-containing semiconductor material comprises single crystal Si, polycrystalline Si, SiGe, amorphous Si or a silicon-on-insulator (SOI).
- 33. The electrical contact of Claim 24 further comprising an oxide layer present near a surface of said substrate.
- 34. The electrical contact of Claim 33 wherein said oxide layer has a thickness of from about 0.1 to about 3.0 nm.
 - 35/The electrical contact of Claim 24 wherein said substrate is doped.--

REMARKS

Favorable consideration and allowance of the claims of the present application, as presently filed, are respectfully requested.

In this preliminary amendment, applicants have canceled original Claims 1-22 herein since those claims are the subject matter of parent application U.S. Serial No. 09/519,897 filed March 6, 2000 and have amended the specification to include information regarding the parent application.

Additionally, applicants have added new claims 25-35 which are directed to specific embodiments of the present invention. Support for the newly added claims is found throughout the specification of the instant application. For example, support for new Claims 25 and 32 is found at Page 7, lines 27-30; support for new Claims 26-28 is found at Page 5, line 29-Page 6, line 4; support for new Claims 29, 30, 33 and 34 is found at Page 7, lines 22-26 and lines 31-32; and support for new Claims 31 and 35 is found at Page 8, line 8.

Since the above amendments to the specification and claims do not introduce any new matter into the application, entry thereof is respectfully requested.

Wherefore, consideration and allowance of the claims of the present application are respectfully requested.

Respectfully submitted,

Leslie S. Szivos

Registration No. 39,394

SCULLY, SCOTT, MURPHY & PRESSER 400 Garden City Plaza Garden City, New York 11530 (516) 742-4343

LSS:tt